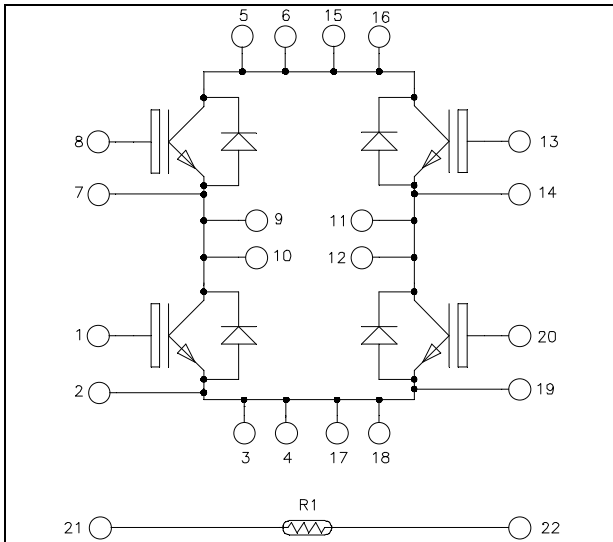


**Full - Bridge  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 75A @ T_c = 80^\circ C$**

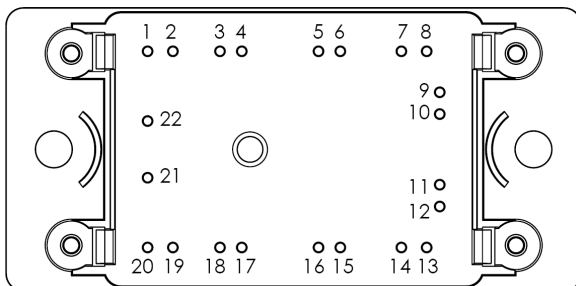


### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration



### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

**All ratings @  $T_j = 25^\circ C$  unless otherwise specified**

### Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	100
		$T_c = 80^\circ C$	75
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	140
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	250
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	150A @ 550V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**Electrical Characteristics (per IGBT)**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	$\mu A$	
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 75A$		$T_j = 25^\circ C$	1.5	1.9	V
				$T_j = 150^\circ C$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu A$	5.0	5.8	6.5	V	
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA	

**Dynamic Characteristics (per IGBT)**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		4620		pF
$C_{oes}$	Output Capacitance			300		
$C_{res}$	Reverse Transfer Capacitance			140		
$Q_G$	Gate charge	$V_{GE} = \pm 15V, I_C = 75A$ $V_{CE} = 300V$		0.8		$\mu C$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ C$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		110		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
$T_f$	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ C$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		120		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
$T_f$	Fall Time			60		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$	$T_j = 25^\circ C$	0.35		mJ
			$T_j = 150^\circ C$	0.6		
$E_{off}$	Turn-off Switching Energy	$I_C = 75A$ $R_G = 4.7\Omega$	$T_j = 25^\circ C$	2.2		mJ
			$T_j = 150^\circ C$	2.6		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 360V$ $t_p \leq 6\mu s ; T_j = 150^\circ C$		380		A
$R_{thJC}$	Junction to Case Thermal Resistance				0.60	$^\circ C/W$

**Reverse diode ratings and characteristics** (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V				250	μA
I <sub>F</sub>	DC Forward current		T <sub>c</sub> = 80°C		75		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 75A V <sub>GE</sub> = 0V	T <sub>j</sub> = 25°C		1.6	2	V
			T <sub>j</sub> = 150°C		1.5		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 75A V <sub>R</sub> = 300V di/dt = 2000A/μs	T <sub>j</sub> = 25°C		100		ns
			T <sub>j</sub> = 150°C		150		
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 75A V <sub>R</sub> = 300V di/dt = 2000A/μs	T <sub>j</sub> = 25°C		3.6		μC
			T <sub>j</sub> = 150°C		7.6		
E <sub>r</sub>	Reverse Recovery Energy	I <sub>F</sub> = 75A V <sub>R</sub> = 300V di/dt = 2000A/μs	T <sub>j</sub> = 25°C		0.85		mJ
			T <sub>j</sub> = 150°C		1.8		
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.98	°C/W

**Temperature sensor NTC**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		22		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>	Resistance tolerance			5	%
ΔB/B	Beta tolerance			3	
B <sub>25/100</sub>	T <sub>25</sub> = 298.16 K		3980		K

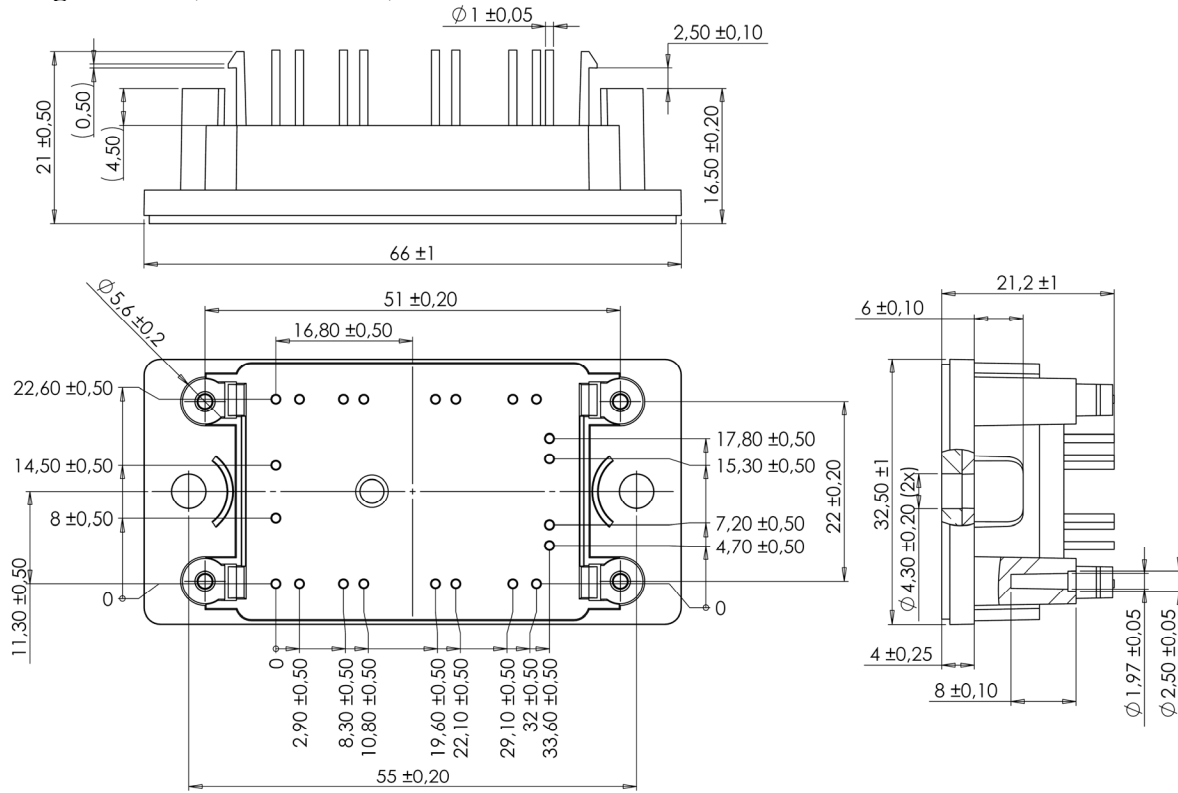
$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

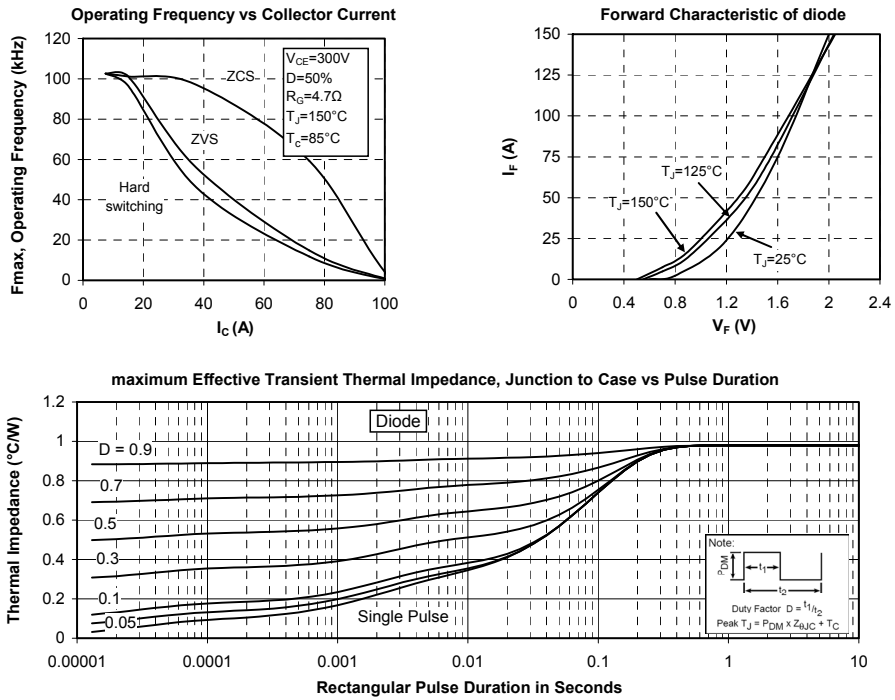
**Thermal and package characteristics**

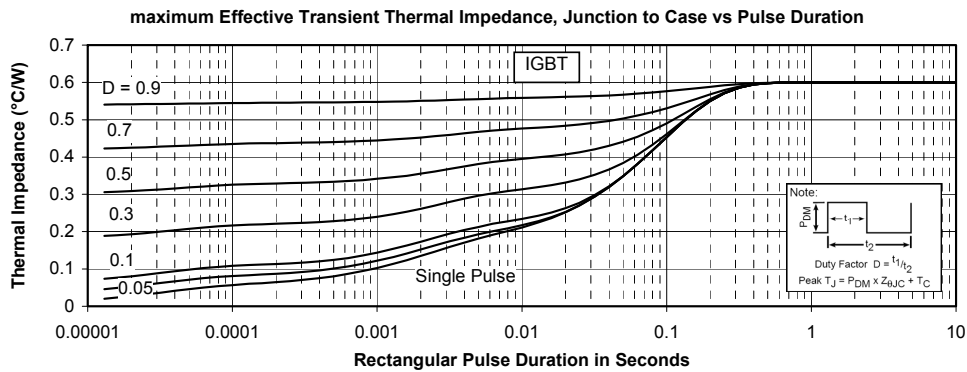
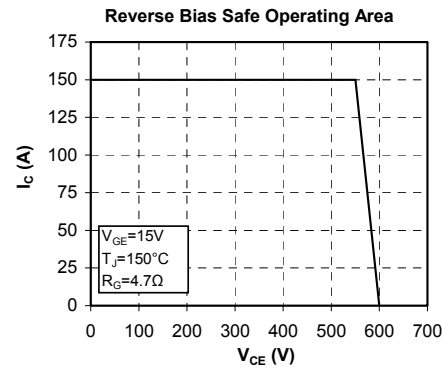
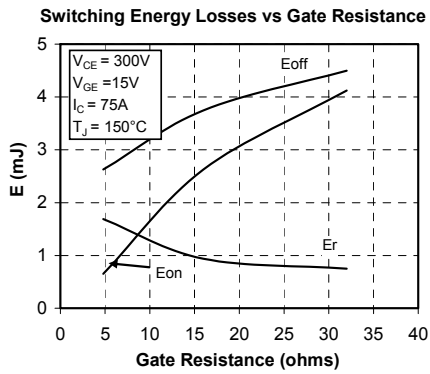
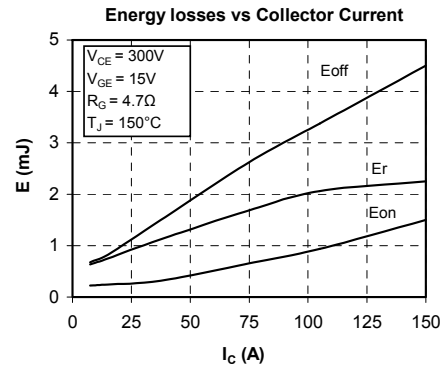
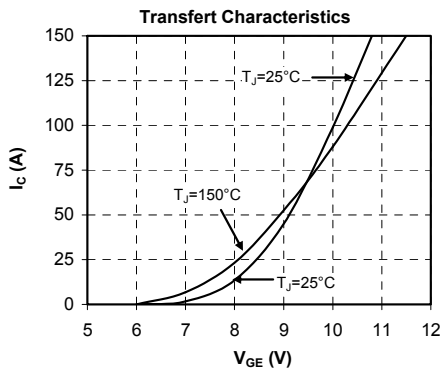
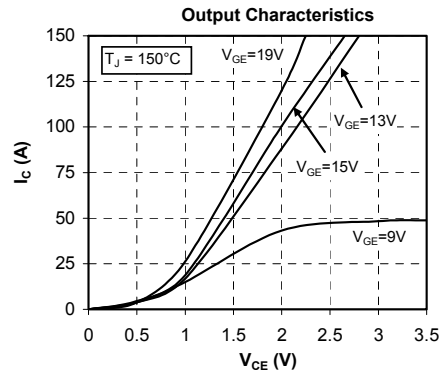
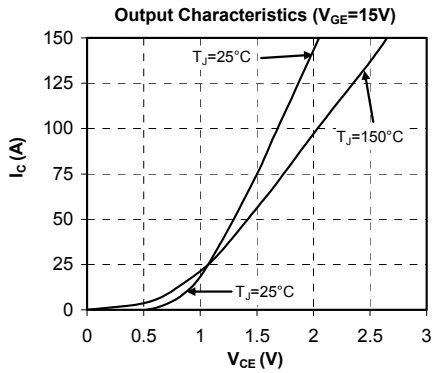
Symbol	Characteristic	Min	Typ	Max	Unit	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		175	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				75	g

## Package outline (dimensions in mm)



## Typical Performance Curve





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